

TMR1162

Nano-Ampere TMR Unipolar Switch

General Description

The TMR1162 is a 200nA ultra-low power magnetic switch sensor. It is a unipolar magnetic switch that integrates TMR and CMOS technology in order to provide a magnetically triggered digital switch with high sensitivity, high speed, and ultra-low power consumption. It integrates a push-pull half-bridge TMR magnetic sensor and CMOS signal processing circuitry within the same package. Designed for use in applications that are both power-critical and performance-demanding, this device includes an on-chip TMR voltage generator for precise magnetic sensing, TMR voltage amplifier and comparator, a Schmitt trigger to provide switching hysteresis for noise rejection, and open-drain output. An internal band gap regulator is used to provide temperature compensated supply voltage for internal circuits, and it allows a wide range of operating supply voltages. The TMR1162 features ultra-low power consumption at 200nA with a fast internal switching frequency at 50Hz. Other important features include accurate switching points, excellent thermal stability, and a wide range of supply voltages. It is available in two packaging form factors: SOT23-3 (P/N TMR1162S), or TO-92S (P/N TMR1162T).

Features and Benefits

- Tunneling Magnetoresistance (TMR) Technology
- Nano-Ampere Ultra-low Power Consumption at 200nA
- Fast Internal Switching Frequency at 50Hz
- Unipolar Operation with High Sensitivity
- Operating Temperature Range from -40°C to 125°C
- Wide Range of Supply Voltages from 1.8V to 5.5V
- Open-drain Output

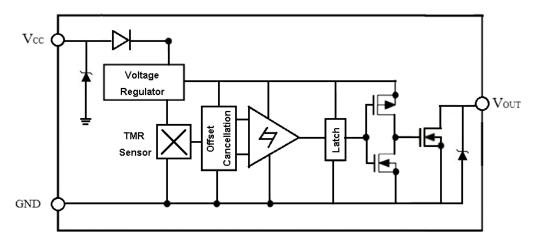
Applications

- Utility Meters including Water, Gas, and Heat Meters
- Speed Sensing and Position Sensing
- Motor and Fan Control
- Power Window

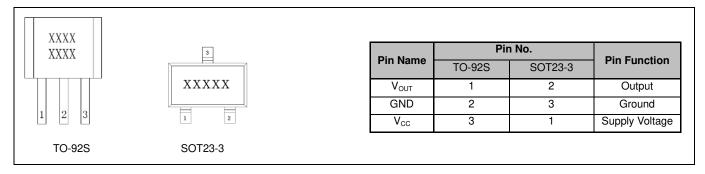


TMR1162S (Left), TMR1162T (Right)

Block Diagram



Pin Configuration



Absolute Maximum Ratings

Characteristic	Symbol	Rating	Units
Supply Voltage	V _{CC}	7	V
Reverse Supply Voltage	V_{RCC}	0.3	V
Output Current	I _{OUTSINK}	20	mA
Magnetic Flux Density	В	4000	G
ESD Level (HBM)	V_{ESD}	4	kV
Operating Ambient Temperature	T _A	-40∼125	°C
Storage Temperature	T_{stg}	-50∼150	°C

Electrical Characteristics (V_{CC}=3.0V, T_A=25°C)

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Supply Voltage	V_{CC}	Operating	1.8	3.0	5.5	V
Output Stress Voltage	V _{stress}				5.5	٧
Output leak Current	I _{leak}	OUT=High, V _{cc} =3V, V _{out} =3V			1	μA
Output Turn-off Resistance	R _{off}	OUT=High		10		МΩ
Output Low Voltage	V _{ol}	OUT=Low, V _{cc} =3V, I _{sink} =3mA			0.1	٧
Output Turn-on Resistance	R _{on}	OUT=Low			10	Ω
Supply Current	I _{cc}	Output open		200		nA
Switching Frequency	F			50		Hz

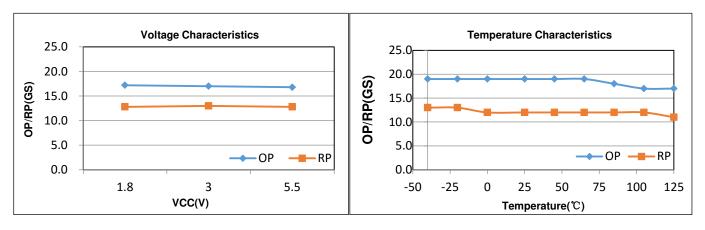
Note: A 1kOhm pull-up resistor is connected between VCC and VOUT, and a $0.1\mu F$ capacitor is connected between VCC and GND during all tests in the table above.

Magnetic Characteristics ($V_{CC} = 3.0V$, $T_A = 25$ °C)

Characteristic	Symbol	Min.	Тур.	Max.	Units
Operate Point	B _{OP}		17		G
Release Point	B_RP		13		G
Hysteresis	B _H		4		G

Note: A 1kOhm pull-up resistor is connected between VCC and VOUT, and a $0.1\mu F$ capacitor is connected between VCC and GND during all tests in the table above.

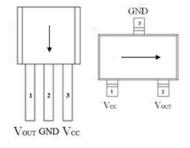
Voltage and Temperature Characteristics



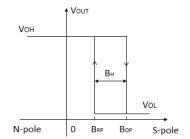
Output Behavior vs. Magnetic Polarity

Magnetic Polarity	Test Conditions	Output	
South Pole for TO92 Package	B > B _{OP}	Low (On)	
	B < B _{RP}	High (Off)	
North Pole for SOT23 Package	B > B _{OP}	Low (On)	
	B < B _{RP}	High (Off)	

Note: The output is "High" when power is turned on under zero magnetic field.



Sensing Direction

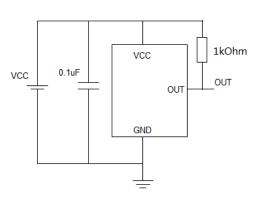


Switching Behavior of TMR1162

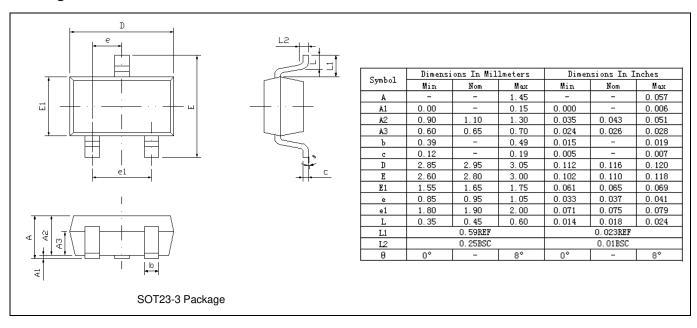
Application Information

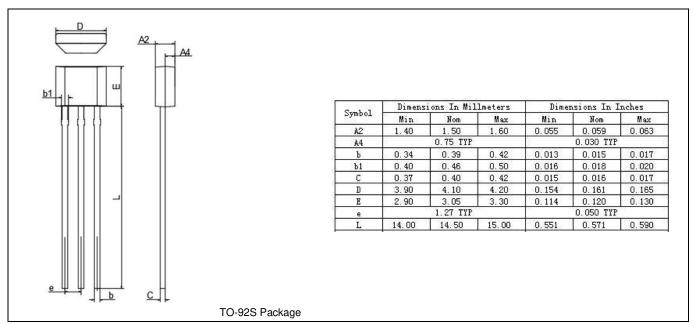
The output of the TMR1162 switches low (turns on) when a magnetic field parallel to the TMR sensor exceeds the operate point threshold, B_{OP} . When the magnetic field is reduced below the release point, B_{RP} , the device output goes high (turns off). The difference between the magnetic operate point and release point is the hysteresis B_H of the device.

It is strongly recommended that an external bypass capacitor be connected in close proximity to the device between the supply and ground to reduce noise. The typical value of the external capacitor is $0.1\mu F$.

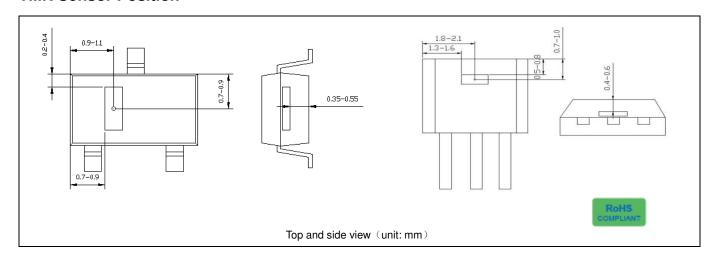


Package Information





TMR Sensor Position





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